

TC74HC05AP, TC74HC05AF

HEX INVERTER (OPEN DRAIN)

The TC74HC05A is a high speed CMOS INVERTER fabricated with silicon gate C²MOS technology.

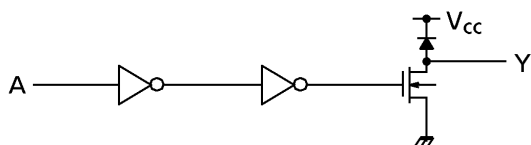
It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. Pin configuration and function are the same as the TC74HC04A, but the TC74HC05A has high performance MOS N-channel transistor (OPEN-DRAIN) outputs.

This device can, therefore, with a suitable pull-up resistors, be used in wired-AND, LED drive and other applications. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

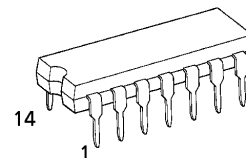
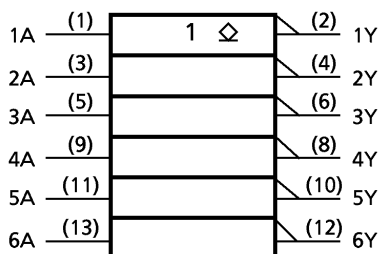
FEATURES:

- High Speed..... $t_{pz} = 8\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability..... 10 LSTTL Loads
- Wide Operating Voltage Range.... $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Open Drain Structure.
- Pin and Function Compatible with 74LS05

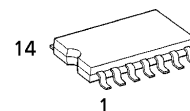
SYSTEM DIAGRAM (per gate)



IEC LOGIC SYMBOL

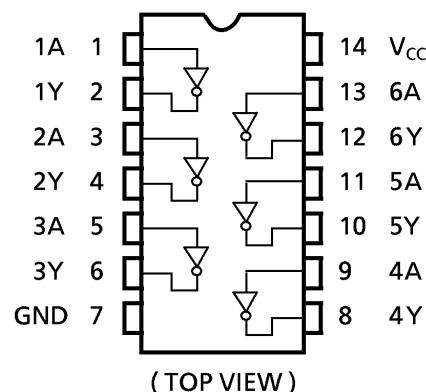


P (DIP14-P-300-2.54)
Weight : 0.96g (Typ.)



F (SOP14-P-300-1.27)
Weight : 0.18g (Typ.)

PIN ASSIGNMENT



TRUTH TABLE

A	Y
L	Z
H	L

Z : High Impedance

980508EBA2

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	+25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ $I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
			4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	
			6.0	—	—	± 0.5	—	± 5.0	
Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$	6.0	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{THL}		—	4	8	ns
Propagation Delay Time	t_{pLZ}	$R_L = 1\text{k}\Omega$	—	8	15	
Propagation Delay Time	t_{pZL}	$R_L = 1\text{k}\Omega$	—	6	15	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C				Ta = −40–85°C		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time	t _{pLZ}	R _L = 1kΩ	2.0	—	20	90	—	115	
			4.5	—	11	18	—	23	
			6.0	—	10	15	—	20	
Propagation Delay Time	t _{pZL}	R _L = 1kΩ	2.0	—	33	90	—	115	
			4.5	—	9	18	—	23	
			6.0	—	7	15	—	20	
Input Capacitance	C _{IN}		—	5	10	—	10	pF	
Output Capacitance	C _{OUT}		—	3	—	—	—		
Power Dissipation Capacitance	C _{PD} (1)		—	7	—	—	—		

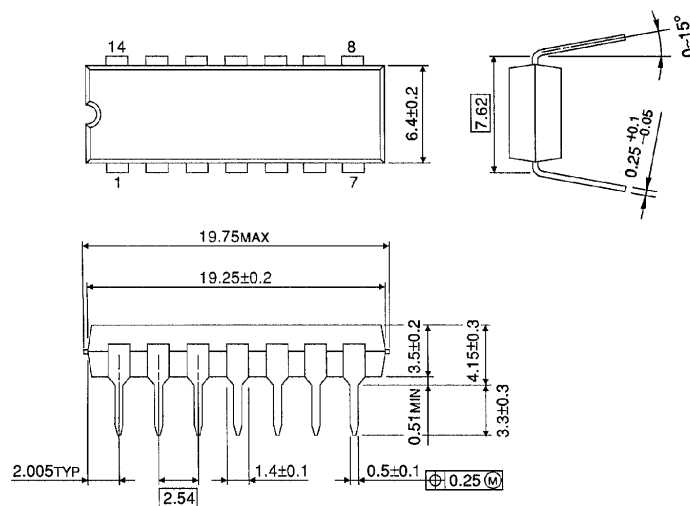
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 6 \text{ (per Gate)}$$

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

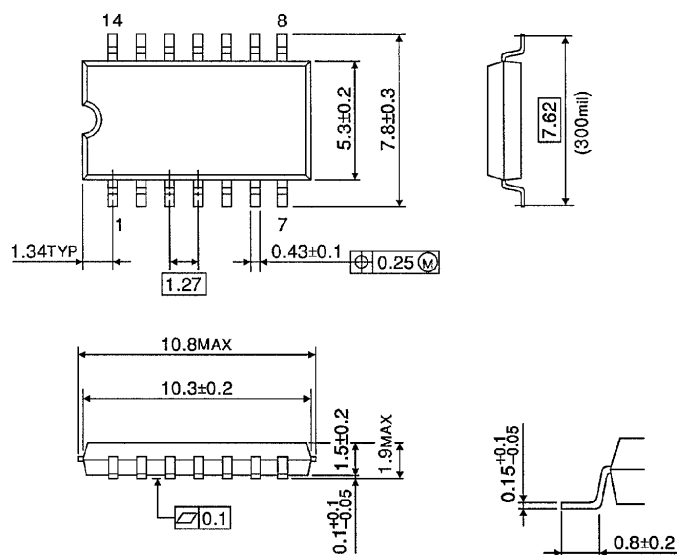
Unit in mm



Weight : 0.96g (Typ.)

SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)